

## Growth and Characterization of CuInTe<sub>2</sub> Thin Films: Review

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**Abstract:** Thin films such as copper indium ditelluride could be used as absorber in low cost solar cell technology. In this study, synthesis and characterization of CuInTe<sub>2</sub> films will be discussed, analyzed and reported. EDAX spectra show that close to ideal stoichiometric (CuInTe<sub>2</sub>) compound. XRD data supported that the formation of tetragonal structure. Optical properties reveal that band gap values range from 0.9-1.4 eV.

**Key words:** Copper indium ditelluride, thin films, solar cell, semiconductor, properties

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### INTRODUCTION

The sizes of thin films were measured in nano and micron meter. Generally, thin films were deposited onto soda lime glass (Kunihiko *et al.*, 2007; Lugo *et al.*, 2017; Hossain *et al.*, 2017; Olgar *et al.*, 2017), indium tin oxide glass (Anuar *et al.*, 2010; Ho *et al.*, 2013; Anuar *et al.*, 2007; Haron *et al.*, 2011; Sabah *et al.*, 2017), stainless steel (Fatas *et al.*, 1987; Cuevas *et al.*, 2016; Sun *et al.*, 2016; Pujari *et al.*, 2016; Dhaygude *et al.*, 2017) and microscope glass slide (Ho *et al.*, 2012; Shaji *et al.*, 2017; Ho, 2014). Now a days, many researchers focus this field (Fajinmi and Adelabu; Zadam; Najamudin) due to thin films were used as optical mass memories, solar cells, hologram recording, solar selecting coatings, sensor devices, laser devices, photo-luminescent and electro-luminescent devices.

Here, the preparation and characterization of CuInTe<sub>2</sub> ternary compounds will be discussed. Furthermore, general properties of films such as optical, morphological structural and compositional will be investigated using various tools.

**Literature review:** X-Ray Diffraction technique (XRD) was used in order to study the structure of films. The XRD patterns show that the formation of tetragonal structure as compared to Joint Committee on Powder Diffraction Standards (JCPDS) data. There are numerous deposition methods were used to produce CuInTe<sub>2</sub> thin films including vertical Bridgman technique and vacuum evaporation method as reported by Mobarak and Shaban (2014), Roy *et al.* (2003), Ananthan and Kasiviswanathan (2009), Kazmerski and Juang (1998) and Boustani *et al.* (1997). The influence of heat treatment on electro deposited CuInTe<sub>2</sub> films was studied by Manorama *et al.* (2016). They found that amorphous structure in as-deposited films. However, the intensities of peaks and

average crystallite sizes were increased for the films treated (80°C) under 5, 30 and 60 min, respectively as shown in XRD patterns. Lakhe and Chaure (2014) have reported the influence of deposition potential on the films. Deposition was carried out in the presence of reference electrode, working electrode and counter electrode. The films prepared at various deposition potentials such as 600, -650, -700 and 750 mV versus Ag/AgCl show amorphous structure. However, CuInTe<sub>2</sub> peaks such as (112), (220)/(204), (312)/(116) could be seen in annealed films (400°C for 1520 min). Dixit *et al.* (2013) have investigated the influence of stirring process on films. The obtained XRD data show that better crystallization for the films prepared under stirring conditions. Also, these films are more oriented in (112) direction if compared to those prepared under without stirring conditions.

### MATERIALS AND METHODS

The influence of temperature (200-260°C for at least 6 h) on CuInTe<sub>2</sub> films was studied by Kim *et al.* (2012). They choose solvothermal deposition technique due to minimal investment and simple method. The films indicate big lumps at temperature of 200°C according to SEM analysis. However, the average grain sizes were increased (from 500 nm to 2 µm) as the temperature was increased from 220-260°C. Chemical spray pyrolysis technique was used to prepare CuInTe<sub>2</sub> films as proposed by Tembhurkar (2016). The morphology of films was studied using Scanning Electron Microscopy (SEM). The larger grain could be seen in annealed films if compared to as deposited films. Also, SEM analysis indicate that good compound formation. Prabukanthan *et al.* (2007) have prepared CuInTe<sub>2</sub> thin films using chemical vapor transport method in the presence of iodine (as the transporting agent). The surface roughness values were measured using Atomic

Force Microscopy (AFM) technique. These values are 9.3 nm (as-deposited films) and 61.2 nm (films irradiated with a fluence of  $1 \times 10^{13}$  ions/cm<sup>2</sup>), respectively.

Transmission electron microscope technique has been used in order to study the morphology of films. The effect of laser fluence and the speed of the laser scan on the films was investigated by Galindo *et al.* (1989). Overall results reflect that obtained films are homogeneous and do not contain any secondary phases. Zedan and El-Menyawy (2016) have prepared CuInTe<sub>2</sub> films using flash evaporation technique. They conclude that illuminated films show better crystallinity conditions and larger sizes if compared to as-deposited films. Also, as-deposited films show the presence of small particles with well distribution of grains on the surface of substrate.

## RESULTS AND DISCUSSION

Energy dispersive X-ray analysis could be employed to determine the composition of thin films prepared under various deposition methods. For example, films with stoichiometry close to 1:1:2 of CuInTe<sub>2</sub> have been successfully grown by using chemical vapor transport method as reported by Prabukanthan and Dhanasekaran (2008). On the other hand, the films prepared using electro deposition method show close to ideal stoichiometry as suggested by Lakhe and Chaurse (2014) and Patil *et al.* (2012).

Lower efficiency (if compared to silicon based solar cell), rare elements (tellurium) and toxicity (tellurium) are some examples of disadvantage of CuInTe<sub>2</sub> films. However, researchers have found that tellurium could be used to replace selenium due to it has high vapor pressure.

Generally, copper indium ditelluride could be categorized in family A<sup>I</sup>-B<sup>III</sup>-C<sup>VI</sup> as suggested by Murali *et al.* (2012). There are many literature reviews and research papers have point out the use of CuInTe<sub>2</sub> films in solar cell applications (Nadenau *et al.*, 1995; Zhang *et al.*, 2013; Orts *et al.*, 2007; Arun *et al.*, 2005; Ali *et al.*, 2017; Assali *et al.*, 1999; Takahiro and Tokio, 2011). Because of many reasons such as band gap values are in the range of 0.9-1.4 eV (Muftah *et al.*, 2010; Chandran *et al.*, 2012; Rai *et al.*, 2017; Sukan *et al.*, 2014; Wasim *et al.*, 1984; Sridevi and Reddy, 1986; Mise and Nakada, 2010; Roy *et al.*, 2002; Ishizaki *et al.*, 2004), higher open circuit voltages, better temperature coefficients, higher absorption coefficient ( $10^5$  cm<sup>-1</sup>) and p-type polycrystalline (Lacruz *et al.*, 1984; Soud *et al.*, 1993; Masoud, 2015; Fitzgerald and Potrous, 1989).

## CONCLUSION

In this research, there are several deposition methods such as electrodeposition, solvothermal method, vacuum evaporation method and chemical spray pyrolysis method were used in order to prepare CuInTe<sub>2</sub> thin films. The experimental results show that tetragonal structure based on XRD data. These films display p-type electrical conductivity and the band gap values in the range of 0.9-1.4 eV.

## ACKNOWLEDGEMENT

Inti International University is gratefully acknowledged for the financial support of this research.

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